**AMENDMENTS TO THE CLAIMS**:

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS**:

**1. (currently amended)** ~~Method~~ A method of selective etching comprising:

[[-]] providing a first material selected from a group A on a substrate;

[[-]] providing a second material selected from a group B on ~~a~~ the substrate;

[[-]] selectively etching said first material with a selectivity of at least 2:1 towards said second material by dispensing a liquid etchant flowing across the substrate surface at a flow ~~sufficient~~ sufficiently fast to generate a mean velocity v parallel to the ~~substrate's~~ surface of the substrate of ~~minimum 0,1m/s~~ at least 0.1 m/s.

**2. (currently amended)** ~~Method~~ The method of claim 1, wherein said liquid etchant is dispensed onto the substrate in a continuous flow and spread over the ~~substrate's~~ surface of the substrate.

**3. (currently amended)** ~~Method~~ The method of claim 2, wherein the point of impact of ~~the~~ a stream of said liquid

etchant stream is moved across the surface of the substrate in a time sequence.

**4. (currently amended)** ~~Method~~ The method of claim 2, wherein said liquid etchant is dispensed at a volume flow of at least ~~0,05~~ 0.05 l/min ~~(especially at least 0,5 l/min)~~.

**5. (currently amended)** ~~Method~~ The method of claim 1, wherein said substrate is rotated while exposed to said liquid etchant.

**6. (currently amended)** ~~Method~~ The method of claim 1, wherein group A comprises materials with a high dielectric constant.

**7. (currently amended)** ~~Method~~ The method of claim 1, wherein group B comprises silicon dioxide[[,]] and silicon.

**8. (currently amended)** ~~Method~~ The method of claim 1, wherein the second material is silicon dioxide and the liquid etchant comprises fluoride ions.

**9. (currently amended)** ~~Method~~ The method of claim 1, wherein said first material is ~~subjected a pretreatment in order~~

pretreated to damage the ~~material's~~ structure of said first material.

**10. (currently amended)** ~~Method~~ The method of claim 9, wherein said pretreatment is performed using an energetic particle bombardment.

**11. (currently amended)** ~~Method~~ The method of claim 1, wherein said liquid etchant is selected from [[a]] the group ~~comprising~~ consisting of:

[[-]] a solution comprising fluoride ions and an additive for lowering dielectric constant of said solution,

[[-]] an acidic[[,]] aqueous solution comprising fluoride ions[[.]]; and

[[-]] an acidic[[,]] aqueous solution comprising fluoride ions and an additive for lowering dielectric number ~~e.g. an alcohol~~.

**12. (currently amended)** ~~Method~~ The method of claim 11, wherein said liquid etchant comprises an analytical concentration of less than ~~0,01~~ 0.01 mol/l of fluoride ions, wherein said analytical concentration is calculated as $F^-$.

**13. (currently amended)** ~~Method~~ The method of claim 1, wherein said liquid etchant comprises fluoride ions and has a pH ~~value of below~~ less than 3.

**14. (new)** The method of claim 2, wherein the liquid etchant is dispensed at a volume flow of at least 0.5 1/min.

**15. (new)** The method of claim 11, wherein the additive for lowering dielectric number, in the acidic aqueous solution comprising fluoride ions, is an alcohol.

**16. (new)** A method of selective etching comprising selectively etching a first material on a substrate with a selectivity of at least 2:1 towards a second material on the substrate, by dispensing a liquid etchant flowing across the substrate surface at a flow sufficiently fast to generate a mean velocity v parallel to the surface of the substrate of at least 0.1 m/s.

**17. (new)** A method of selective etching comprising:

providing a first material on a substrate, wherein said first material is $HfO_2$ or $ZrO_2$, and said first material is pretreated with an energetic particle bombardment;

providing a second material on the substrate; and

selectively etching said first material with a selectivity of at least 2:1 towards said second material by dispensing a liquid etchant flowing across the substrate surface at a flow sufficiently fast to generate a mean velocity v parallel to the surface of the substrate of at least 0.1 m/s.